

ABSTRACT OF THE DISCLOSURE

The method for fabricating the semiconductor device comprises the step of forming an insulating film 14 having an opening 18; the step of forming an organic resist film 20a; the step of forming over the organic resist film 20a a mask film 20b having etching characteristics different from those of the organic resist film 20a; the step of forming an opening in the mask film 20b; and the step of etching the organic resist film 20a with the mask film 20b as the mask. In the step of etching the organic resist film, the organic resist film 20a is etched with a mixed gas of nitrogen gas and oxygen gas.